



## ELC-630-15

Radiation	Type	Electrodes
Red	AlGaInP / Si	P (anode) up

	<ul style="list-style-type: none"> <li>- High luminous intensity</li> <li>- Thin film structure</li>   <li>- Typ. dimension 350±25 µm</li> <li>- Typ. thickness 100±15 µm</li> </ul>
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### Absolute Maximum Ratings

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Symbol	Typ	Unit
Forward DC current	I <sub>F</sub>	≤70	mA
Reverse voltage	V <sub>R</sub>	≤10	V
Junction temperature	T <sub>J</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-40 ~ +85	°C

### Optical and Electrical Characteristics

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> =10 µA	V <sub>F</sub>	1.3			V
Forward voltage	I <sub>F</sub> =20 mA	V <sub>F</sub>		2.1	2.5	V
Reverse current	V <sub>R</sub> = 10V	I <sub>R</sub>			5	µA
Luminous intensity*	I <sub>F</sub> =20 mA	I <sub>V</sub>		600		mcd
Peak wavelength	I <sub>F</sub> =20 mA	λ <sub>p</sub>		631		nm
Dominant wavelength	I <sub>F</sub> =20 mA	λ <sub>p</sub>		624		nm
FWHM	I <sub>F</sub> =20 mA	Δλ <sub>0.5</sub>		20		nm

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire bond side up



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.